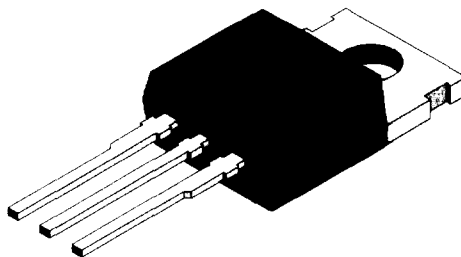


Silicon NPN High Voltage Switching Transistor

Features

- HIGH SPEED technology
- High reverse voltage
- Power dissipation $P_{tot} = 57 \text{ W}$
- Glass passivation
- Short switching times



95 9640

Applications

Electronic lamp ballast circuits
Switch-mode power supplies

Absolute Maximum Ratings

$T_{case} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test Conditions	Type	Symbol	Value	Unit
Collector-emitter voltage		TE13004	V_{CEO}	300	V
		TE13005	V_{CEO}	400	V
		TE13004	V_{CES}	600	V
		TE13005	V_{CES}	700	V
Emitter-base voltage			V_{EBO}	9	V
Collector current			I_C	6	A
Collector peak current			I_{CM}	8	A
Base current			I_B	2	A
Base peak current			I_{BM}	4	A
Total power dissipation	$T_{case} \leq 25^{\circ}\text{C}$		P_{tot}	57	W
Junction temperature			T_j	150	$^{\circ}\text{C}$
Storage temperature range			T_{stg}	-65 to +150	$^{\circ}\text{C}$

Maximum Thermal Resistance

$T_{case} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Junction case		R_{thJC}	2.2	K/W

Electrical Characteristics

$T_{\text{case}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Collector cut-off current	$V_{\text{CE}} = 600 \text{ V}$	TE13004	I_{CES}			50	μA
	$V_{\text{CE}} = 700 \text{ V}$	TE13005	I_{CES}			50	μA
	$V_{\text{CE}} = 600 \text{ V}; T_{\text{case}} = 150^{\circ}\text{C}$	TE13004	I_{CES}			0.5	mA
	$V_{\text{CE}} = 700 \text{ V}; T_{\text{case}} = 150^{\circ}\text{C}$	TE13005	I_{CES}			0.5	mA
Collector-emitter breakdown voltage (figure 1)	$I_{\text{C}} = 100 \text{ mA}; L = 125 \text{ mH}; I_{\text{measure}} = 100 \text{ mA}$	TE13004	$V_{(\text{BR})\text{CEO}}$	300			V
		TE13005	$V_{(\text{BR})\text{CEO}}$	400			V
Emitter-base breakdown voltage	$I_{\text{E}} = 1 \text{ mA}$		$V_{(\text{BR})\text{EBO}}$	9			V
Collector-emitter saturation voltage	$I_{\text{C}} = 2 \text{ A}; I_{\text{B}} = 0.5 \text{ A}$		V_{CEsat}			0.6	V
Base-emitter saturation voltage	$I_{\text{C}} = 2 \text{ A}; I_{\text{B}} = 0.5 \text{ A}$		V_{BEsat}			1.6	V
DC forward current transfer ratio	$V_{\text{CE}} = 5 \text{ V}; I_{\text{C}} = 10 \text{ mA}$		h_{FE}	10			
	$V_{\text{CE}} = 5 \text{ V}; I_{\text{C}} = 1 \text{ A}$		h_{FE}	10			
	$V_{\text{CE}} = 5 \text{ V}; I_{\text{C}} = 4 \text{ A}$		h_{FE}	4			
Gain bandwidth product	$V_{\text{CE}} = 10 \text{ V}; I_{\text{C}} = 500 \text{ mA}; f = 1 \text{ MHz}$		f_{T}	4			MHz

Switching Characteristics

$T_{case} = 25^{\circ}C$, unless otherwise specified

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Resistive load (figure 2)							
Turn on time	$I_C = 2\text{ A}; I_{B1} = -I_{B2} = 0.4\text{ A};$		t_{on}		0.25	0.4	μs
Storage time	$V_S = 125\text{ V}$		t_s		1.5	2.5	μs
Fall time			t_f		0.2	0.3	μs
Inductive load (figure 3)							
Storage time	$I_C = 2\text{ A}; I_{B1} = 0.4\text{ A};$ $L = 200\text{ }\mu H; V_{clamp} = 300\text{ V};$		t_s		1.2	2	μs
Cross over time	$-V_{BE} = 5\text{ V}; T_{case} = 100^{\circ}C$		t_c		0.4	0.7	μs

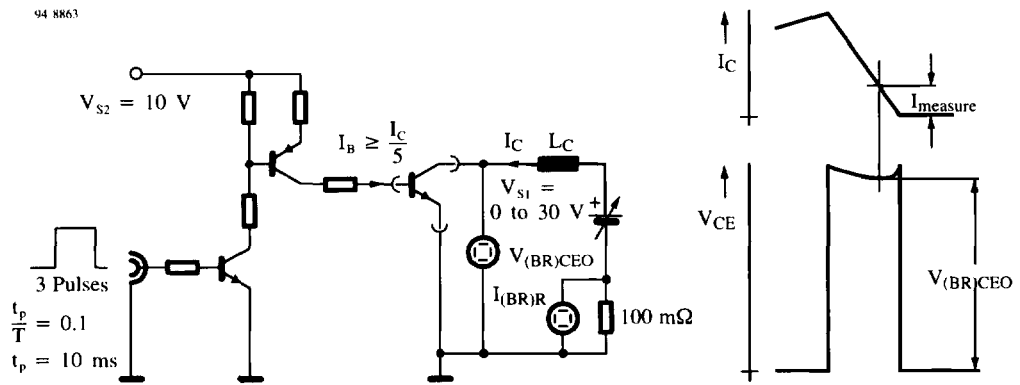
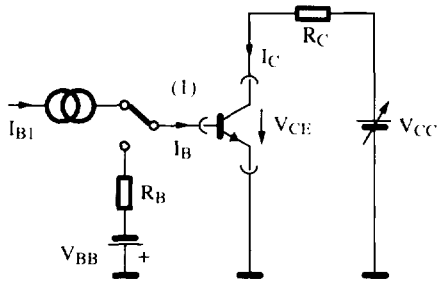


Figure 1. Test circuit for $V_{(BR)CEO}$

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(1) Fast electronic switch

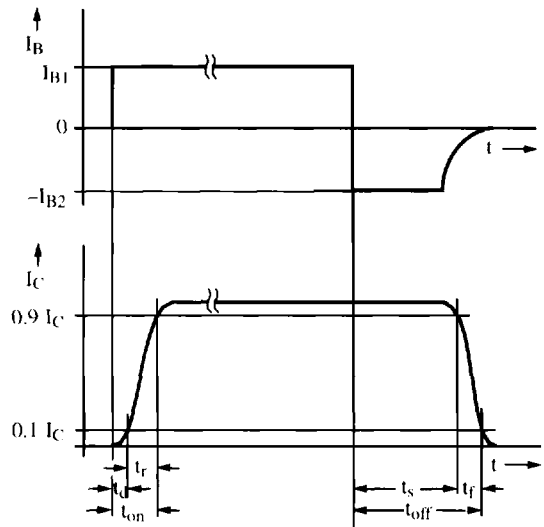
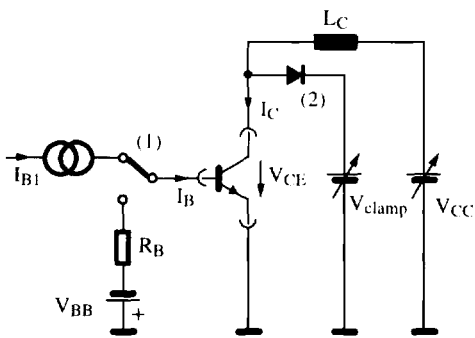


Figure 2. Test circuit for switching characteristics – resistive load

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(1) Fast electronic switch
(2) Fast recovery rectifier

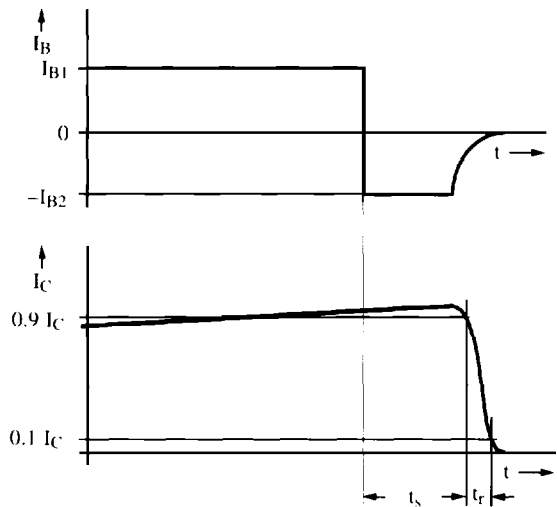


Figure 3. Test circuit for switching characteristics – inductive load

Typical Characteristics ($T_{case} = 25^{\circ}C$ unless otherwise specified)

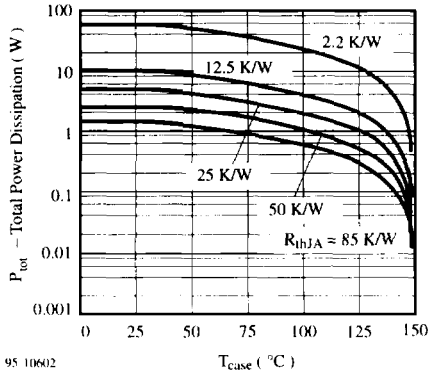


Figure 4. P_{tot} vs. T_{case}

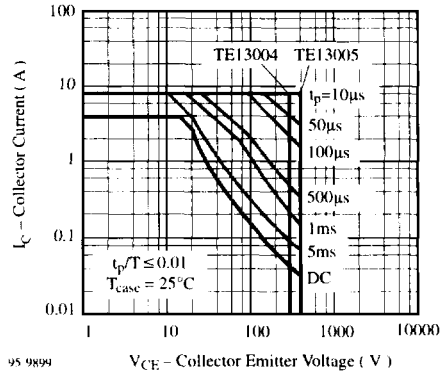


Figure 7. I_C vs. V_{CE}

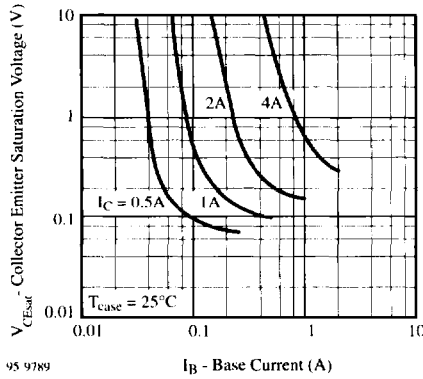


Figure 5. $V_{CE(sat)}$ vs. I_B

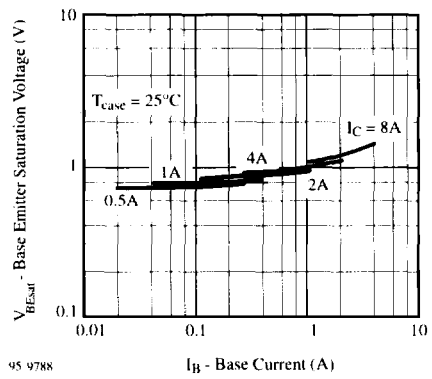


Figure 8. $V_{BE(sat)}$ vs. I_B

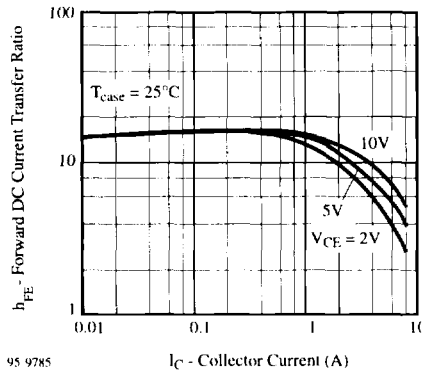


Figure 6. h_{FE} vs. I_C

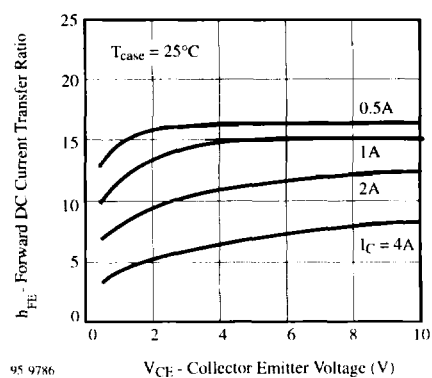


Figure 9. h_{FE} vs. V_{CE}

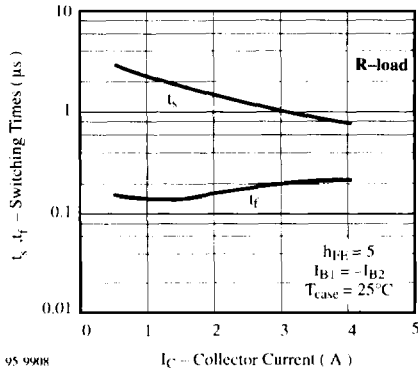


Figure 10. t_s, t_f vs. I_C

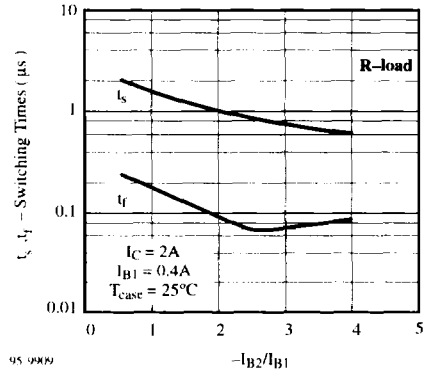


Figure 13. t_s, t_f vs. $-I_{B2}/I_{B1}$

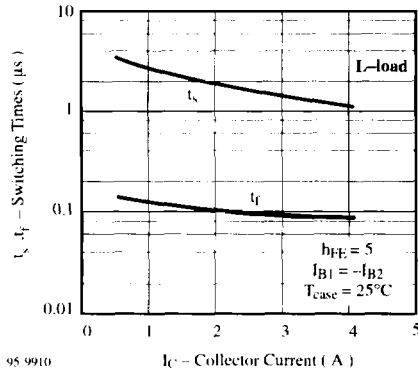


Figure 11. t_s, t_f vs. I_C

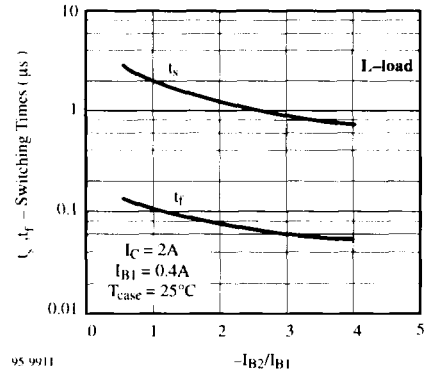


Figure 14. t_s, t_f vs. $-I_{B2}/I_{B1}$

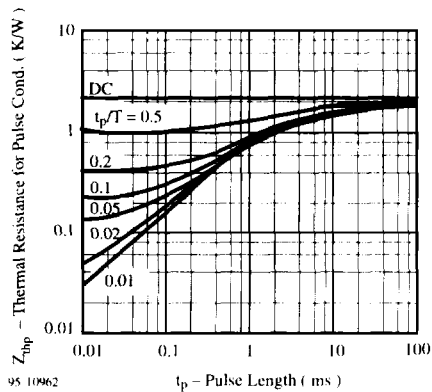


Figure 12. Z_{thp} vs. t_p

Dimensions in mm

